FIG. 1A

FIG. 1B

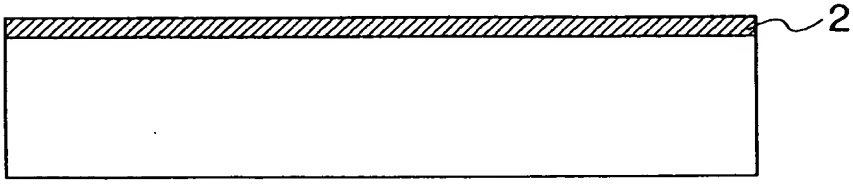

FIG. 1C

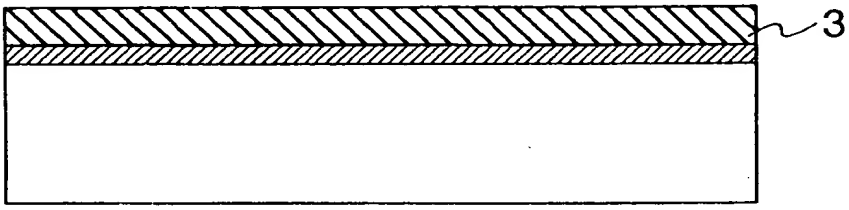

FIG. 1D

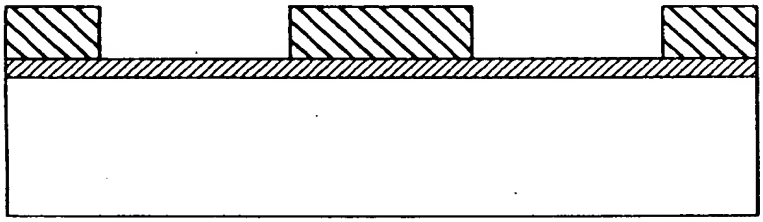

FIG. 1E

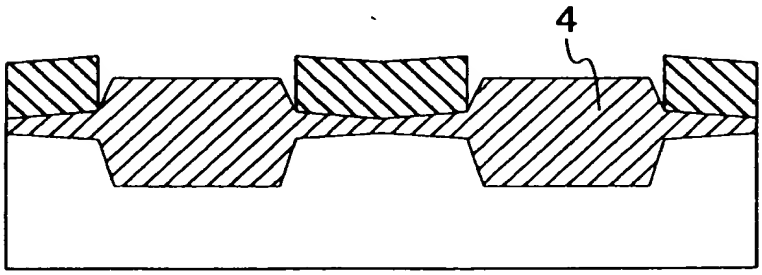

FIG. 1F

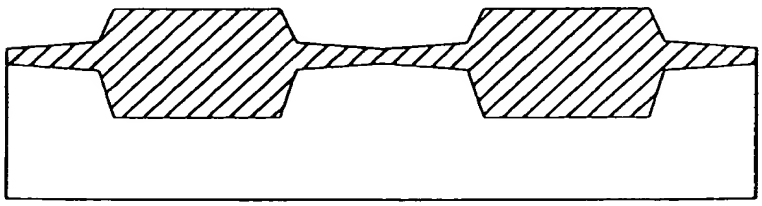

FIG. 2A

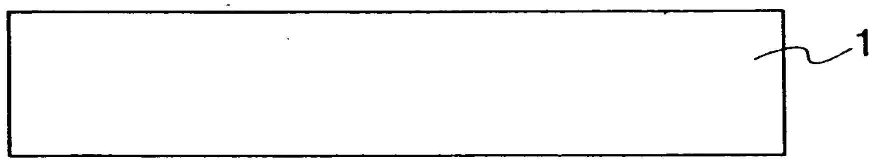

FIG. 2B

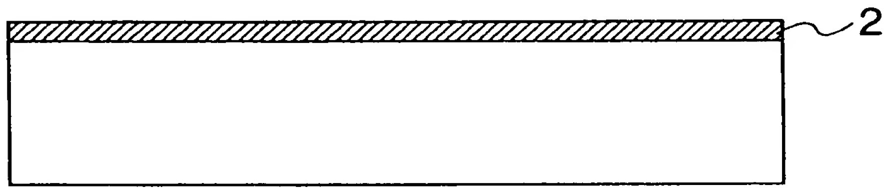

FIG. 2C

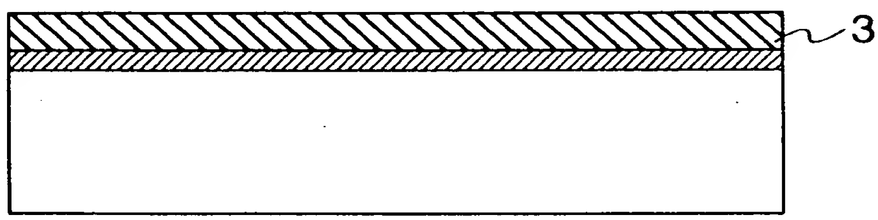

FIG. 2D

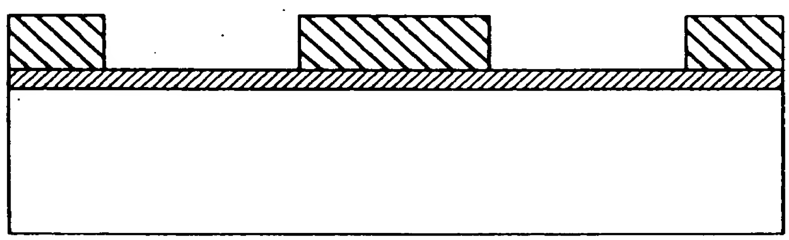

FIG. 2E

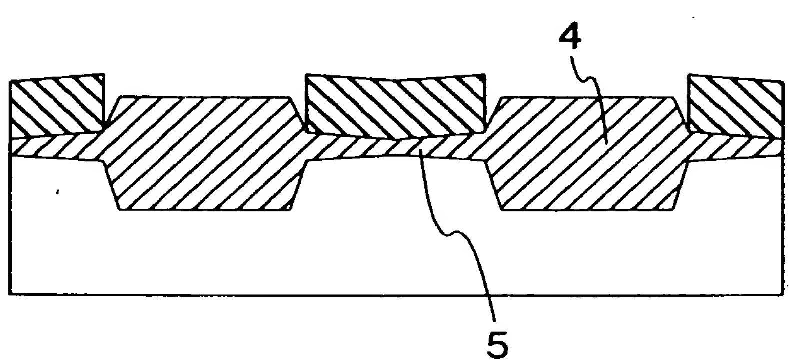

FIG. 3

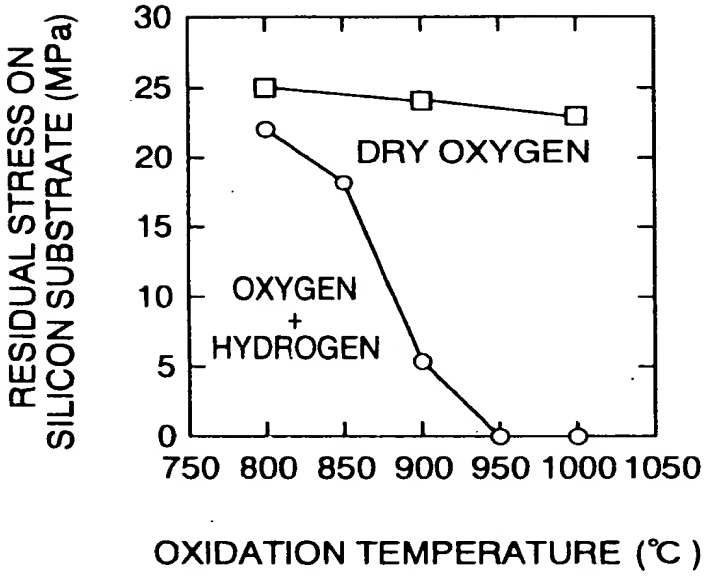
RESIDUAL STRESS ON SILICON SUBSTRATE (MPa)
30
25
20
15
10
5
0
DRY OXYGEN
OXYGEN
+
HYDROGEN
750 800 850 900 950 1000 1050
OXIDATION TEMPERATURE (℃)

FIG. 4

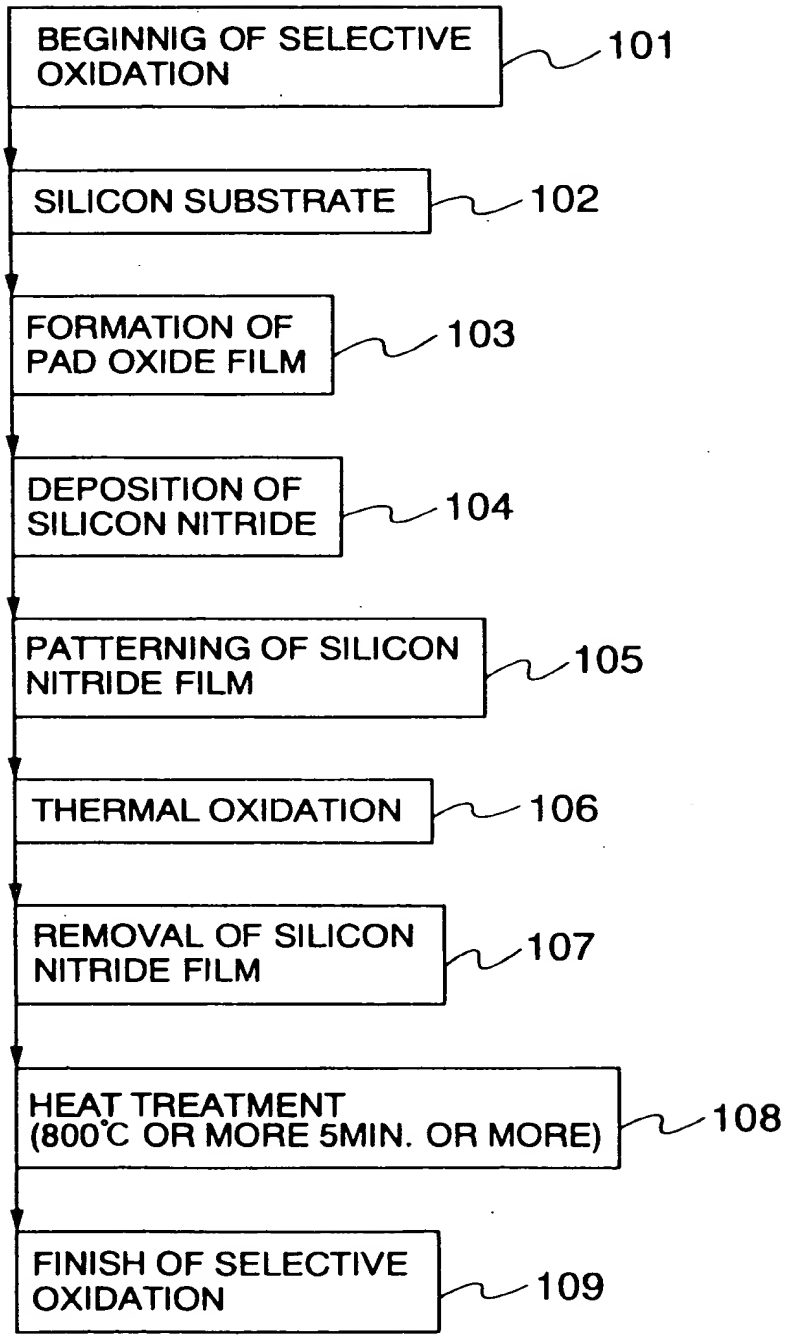
BEGINNIG OF SELECTIVE OXIDATION
101
SILICON SUBSTRATE
102
FORMATION OF PAD OXIDE FILM
103
DEPOSITION OF SILICON NITRIDE
104
PATTERNING OF SILICON NITRIDE FILM
105
THERMAL OXIDATION
106
REMOVAL OF SILICON NITRIDE FILM
107
HEAT TREATMENT (800℃ OR MORE 5MIN. OR MORE)
108
FINISH OF SELECTIVE OXIDATION
109

FIG. 5A

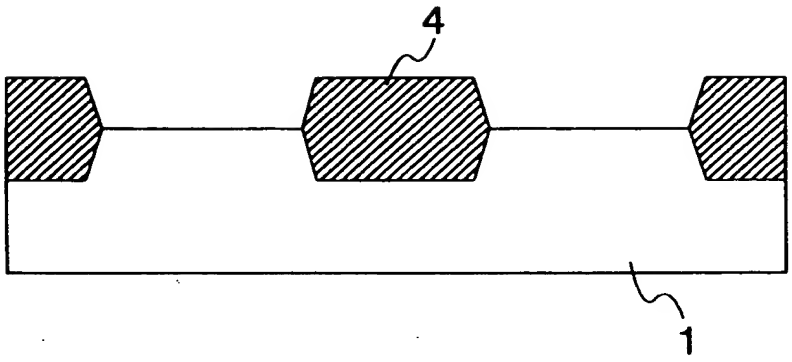

FIG. 5B

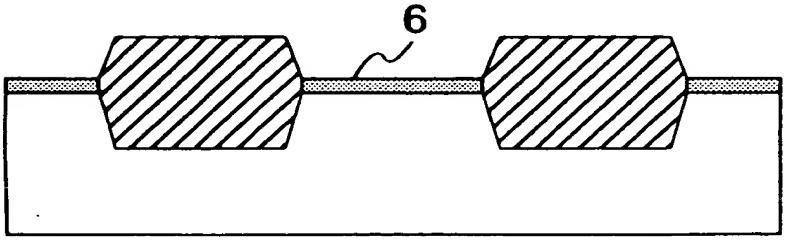

FIG. 6

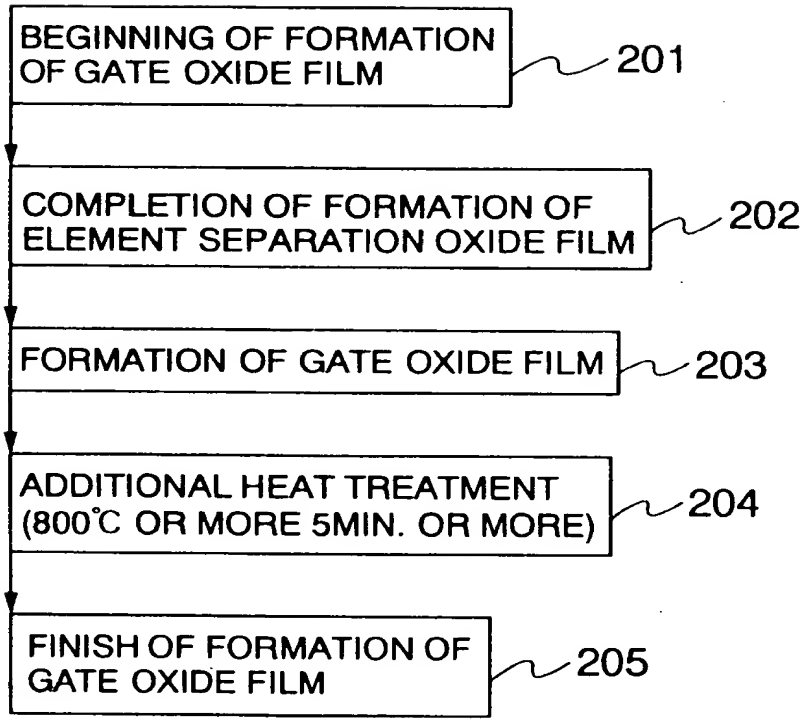
BEGINNING OF FORMATION OF GATE OXIDE FILM
201
COMPLETION OF FORMATION OF ELEMENT SEPARATION OXIDE FILM
202
FORMATION OF GATE OXIDE FILM
203
ADDITIONAL HEAT TREATMENT (800℃ OR MORE 5MIN. OR MORE)
204
FINISH OF FORMATION OF GATE OXIDE FILM
205

FIG. 7A

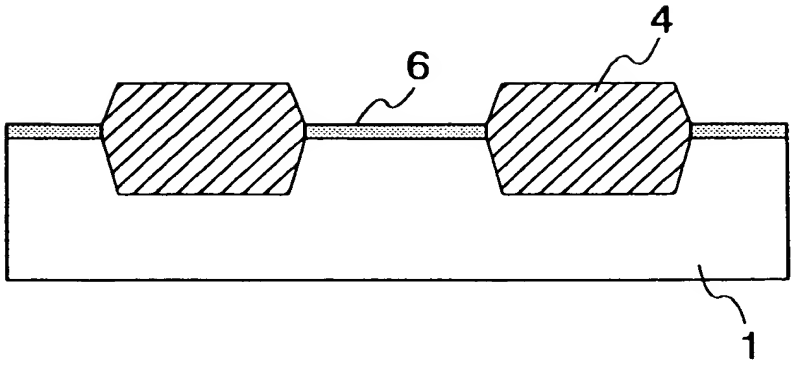

FIG. 7B

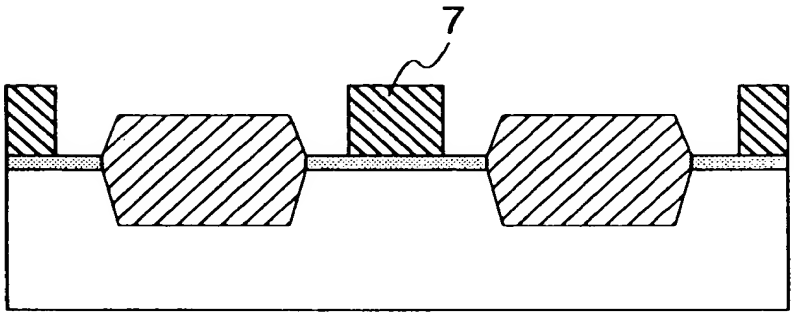

FIG. 7C

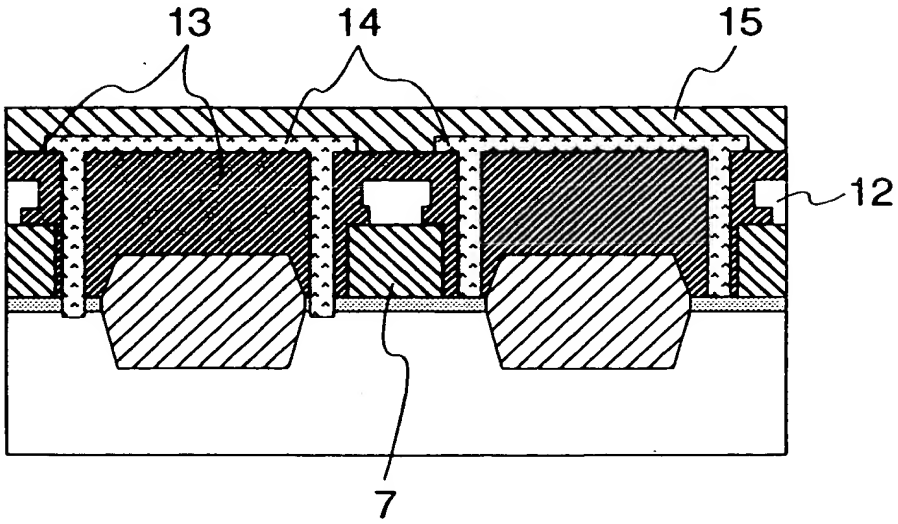

FIG. 8

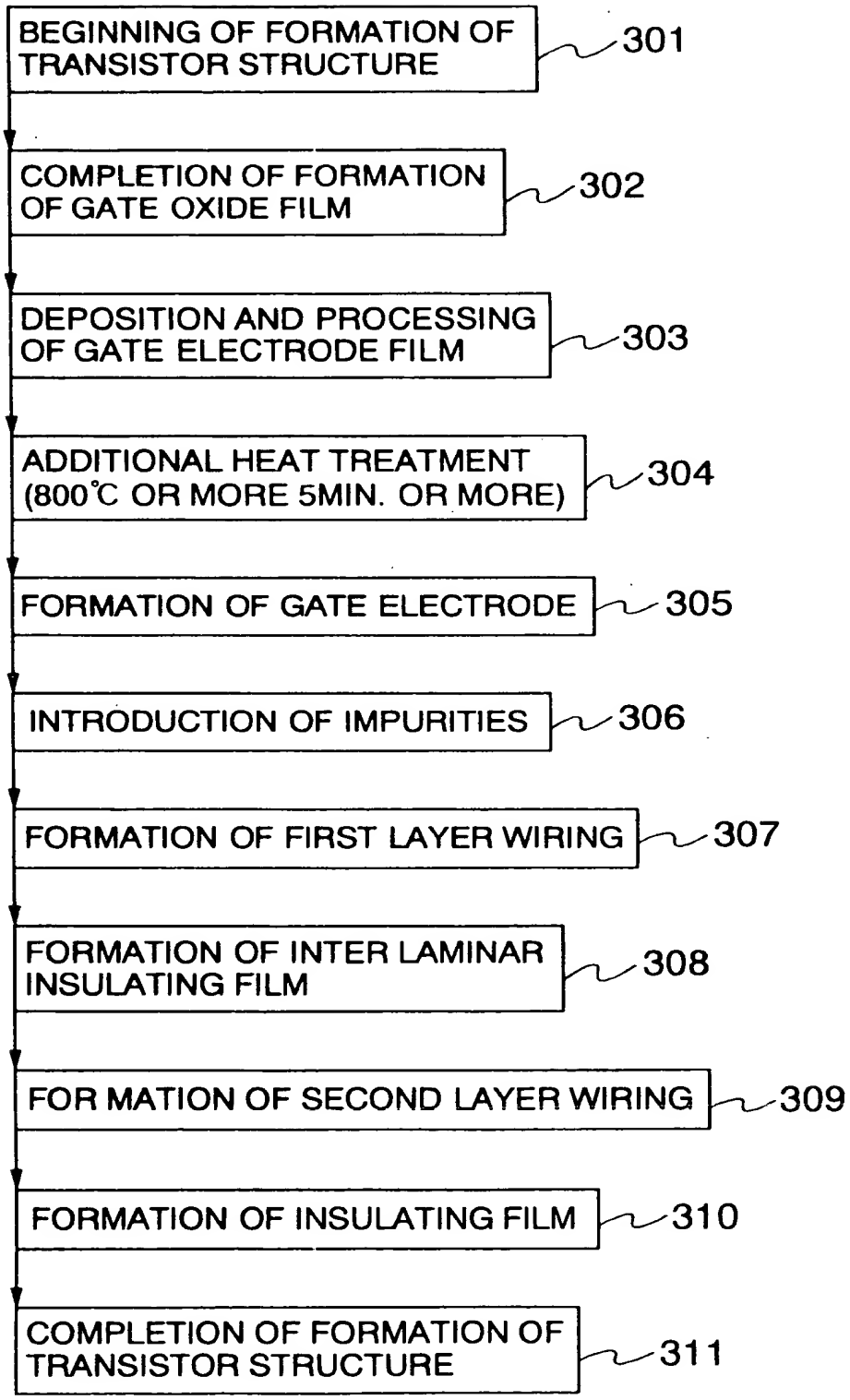

FIG. 9A

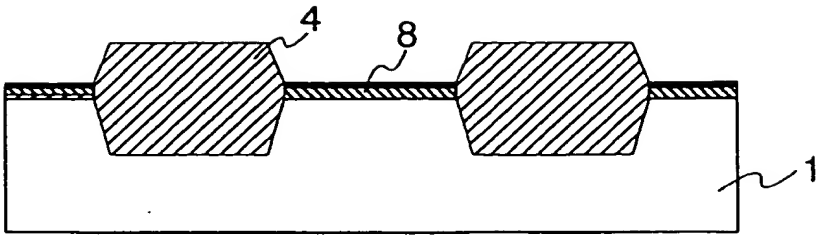

FIG. 9B

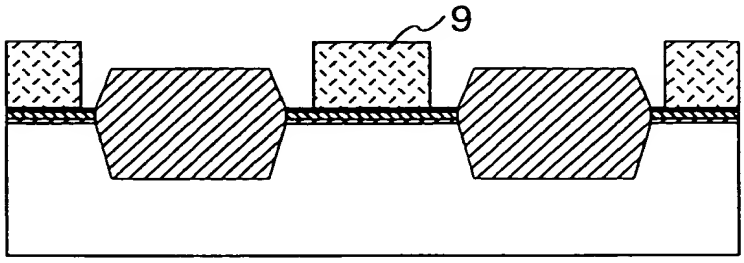

FIG. 9C

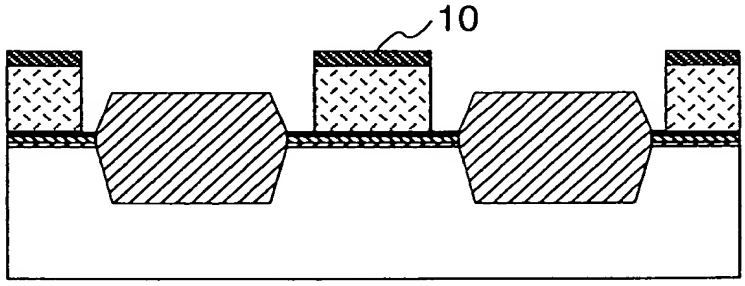

FIG. 9D

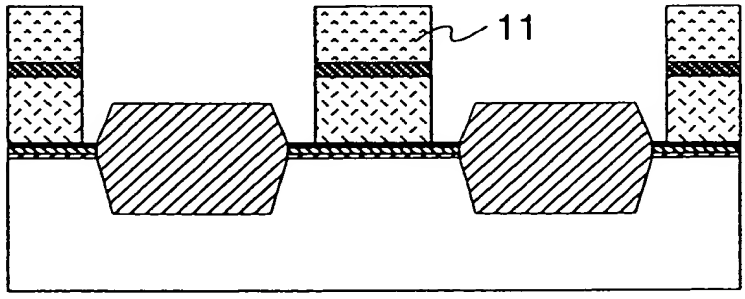

FIG. 9E

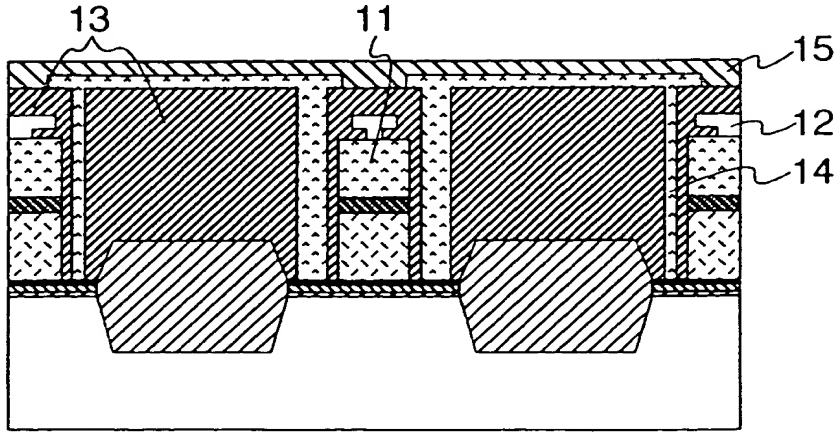

FIG. 10